162162

A B S T R A C T

METHOD FOR REDUCING SURFACE RUGOSITY

The invention provides a method of reducing the roughness of the free surface of a wafer of semiconductor material, said method comprising a stage of annealing in order to smooth said free surface, the method being characterized in that the stage of reducing the free surface roughness comprises a single smoothing annealing operation implemented in the form of rapid thermal annealing under an atmosphere made up exclusively of pure argon. The invention also provides a structure made by such a method.

G00002

Translation of the title and the abstract as they were when originally filed by the Applicant. No account has been taken of any changes that may have been made subsequently by the PCT Authorities acting ex officio, e.g. under PCT Rules 37.2, 38.2, and/or 48.3.